

N-Channel Enhancement Mode MOSFET

Features

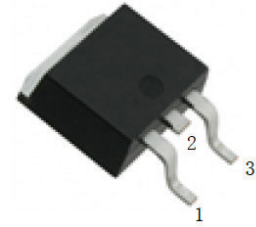
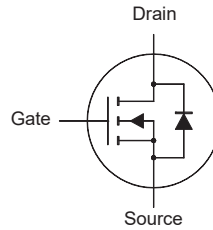
- AEC-Q101 Qualified
- Low gate charge
- Fast switching speed
- Halogen and Antimony Free(HAF), RoHS compliant

Applications

- Power management for UPS and inverter systems

Key Parameters

Parameter	Value	Unit
BV_{DSS}	40	V
$R_{DS(ON)}$ Max	6 @ $V_{GS} = 10$ V	m Ω
$V_{GS(th)}$ typ	2.5	V
Q_g typ	110 @ $V_{GS} = 10$ V	nC



1.Gate 2.Drain 3.Source
TO-252 Plastic Package

Absolute Maximum Ratings (at $T_a = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current	I_D	90 57	A
Peak Drain Current, Pulsed ¹⁾	I_{DM}	480	A
Avalanche Current	I_{AS}	25	A
Single-Pulse Avalanche Energy ²⁾	E_{AS}	312	mJ
Power Dissipation	P_D	75	W
Operating Junction and Storage Temperature Range	T_j, T_{stg}	- 55 to + 175	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Max.	Unit
Thermal Resistance from Junction to Case	$R_{\theta JC}$	2	$^\circ\text{C/W}$
Thermal Resistance from Junction to Ambient ³⁾	$R_{\theta JA}$	40	$^\circ\text{C/W}$

¹⁾ Pulse Test: Pulse Width $\leq 100 \mu\text{s}$, Duty Cycle $\leq 2\%$, Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)} = 175^\circ\text{C}$.

²⁾ Limited by $T_{J(MAX)}$, starting $T_J = 25^\circ\text{C}$, $L = 1$ mH, $R_g = 25 \Omega$, $I_D = 25$ A, $V_{GS} = 10$ V.

³⁾ Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate in still air.

Characteristics at $T_a = 25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit
STATIC PARAMETERS					
Drain-Source Breakdown Voltage at $I_D = 250 \mu\text{A}$	BV_{DSS}	40	-	-	V
Drain-Source Leakage Current at $V_{DS} = 40 \text{ V}$	I_{DSS}	-	-	1	μA
Gate Leakage Current at $V_{GS} = \pm 20 \text{ V}$	I_{GSS}	-	-	± 100	nA
Gate-Source Threshold Voltage at $V_{DS} = V_{GS}$, $I_D = 250 \mu\text{A}$	$V_{GS(th)}$	2	-	4	V
Drain-Source On-State Resistance at $V_{GS} = 10 \text{ V}$, $I_D = 40 \text{ A}$	$R_{DS(on)}$	-	4.6	6	m Ω
DYNAMIC PARAMETERS					
Gate Resistance at $V_{DS} = 0 \text{ V}$, $f = 1 \text{ MHz}$	R_g	-	1	-	Ω
Input Capacitance at $V_{GS} = 0 \text{ V}$, $V_{DS} = 20 \text{ V}$, $f = 1 \text{ MHz}$	C_{iss}	-	5660	-	pF
Output Capacitance at $V_{GS} = 0 \text{ V}$, $V_{DS} = 20 \text{ V}$, $f = 1 \text{ MHz}$	C_{oss}	-	624	-	pF
Reverse Transfer Capacitance at $V_{GS} = 0 \text{ V}$, $V_{DS} = 20 \text{ V}$, $f = 1 \text{ MHz}$	C_{rss}	-	398	-	pF
Gate charge total at $V_{DD} = 20 \text{ V}$, $V_{GS} = 10 \text{ V}$, $I_D = 40 \text{ A}$	Q_g	-	110	-	nC
Gate to Source Charge at $V_{DD} = 20 \text{ V}$, $V_{GS} = 10 \text{ V}$, $I_D = 40 \text{ A}$	Q_{gs}	-	25	-	nC
Gate to Drain Charge at $V_{DD} = 20 \text{ V}$, $V_{GS} = 10 \text{ V}$, $I_D = 40 \text{ A}$	Q_{gd}	-	29	-	nC
Turn-On Delay Time at $V_{DD} = 20 \text{ V}$, $V_{GS} = 10 \text{ V}$, $I_D = 40 \text{ A}$, $R_g = 4.7 \Omega$	$t_{d(on)}$	-	45	-	ns
Turn-On Rise Time at $V_{DD} = 20 \text{ V}$, $V_{GS} = 10 \text{ V}$, $I_D = 40 \text{ A}$, $R_g = 4.7 \Omega$	t_r	-	84	-	ns
Turn-Off Delay Time at $V_{DD} = 20 \text{ V}$, $V_{GS} = 10 \text{ V}$, $I_D = 40 \text{ A}$, $R_g = 4.7 \Omega$	$t_{d(off)}$	-	34	-	ns
Turn-Off Fall Time at $V_{DD} = 20 \text{ V}$, $V_{GS} = 10 \text{ V}$, $I_D = 40 \text{ A}$, $R_g = 4.7 \Omega$	t_f	-	13	-	ns
Body-Diode PARAMETERS					
Drain-Source Diode Forward Voltage at $I_s = 1 \text{ A}$, $V_{GS} = 0 \text{ V}$	V_{SD}	-	-	1.3	V
Body-Diode Continuous Current	I_s	-	-	90	A
Body-Diode Continuous Current, Pulsed	I_{SM}	-	-	480	A
Body Diode Reverse Recovery Time at $I_s = 40 \text{ A}$, $di/dt = 100 \text{ A} / \mu\text{s}$	t_{rr}	-	23	-	ns
Body Diode Reverse Recovery Charge at $I_s = 40 \text{ A}$, $di/dt = 100 \text{ A} / \mu\text{s}$	Q_{rr}	-	17	-	nC

Electrical Characteristics Curves

Fig. 1 Typical Output Characteristics

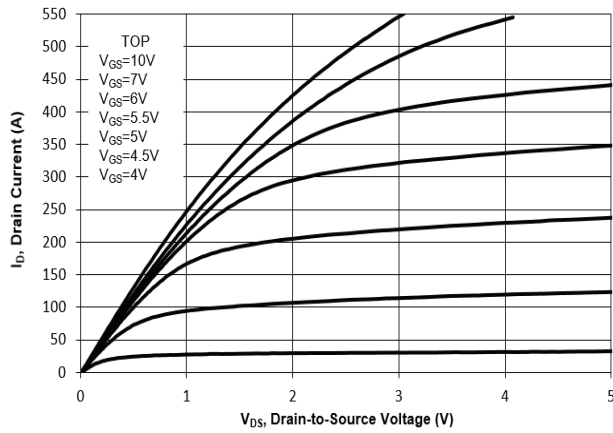


Fig. 2 Typical Transfer Characteristics

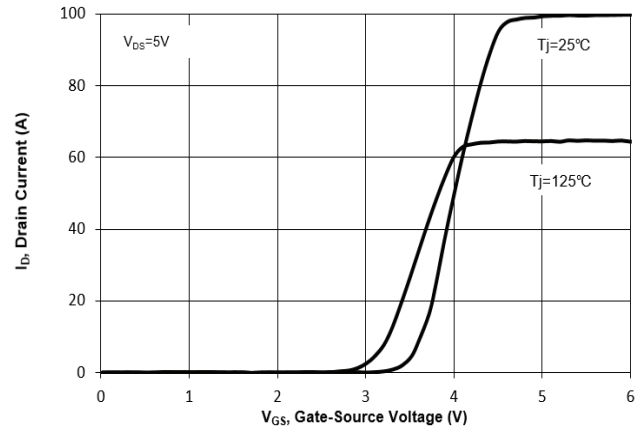


Fig. 3 on-Resistance vs. Drain Current

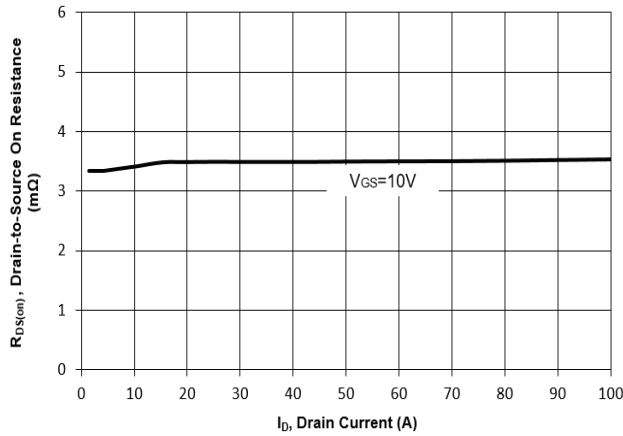


Fig. 4 on-Resistance vs. Gate to Source Voltage

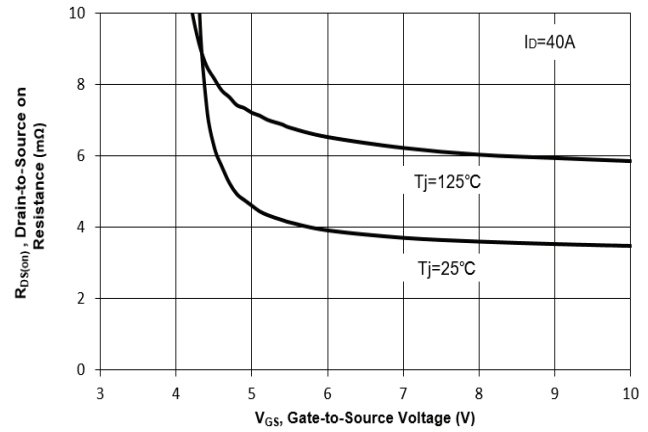


Fig. 5 on-Resistance vs. T_J

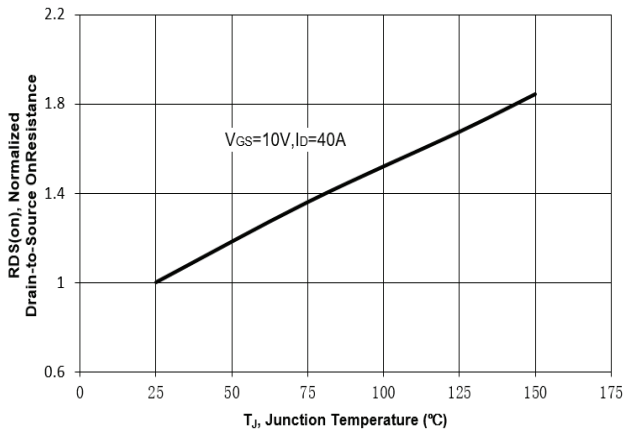
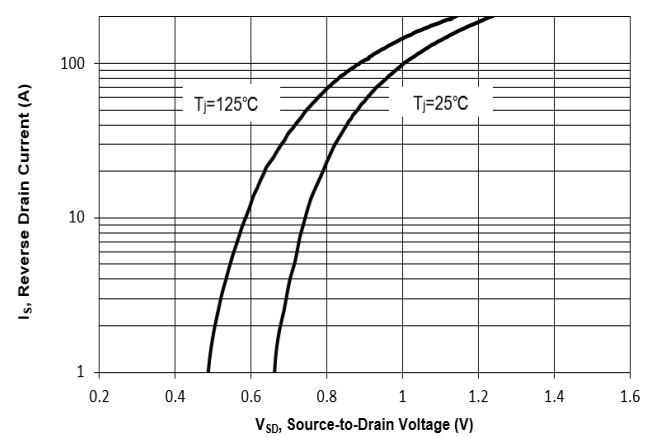


Fig. 6 Typical Body-Diode Forward Characteristics



Electrical Characteristics Curves

Fig. 13 Normalized Maximum Transient Thermal Impedance($Z_{\theta JC}$)

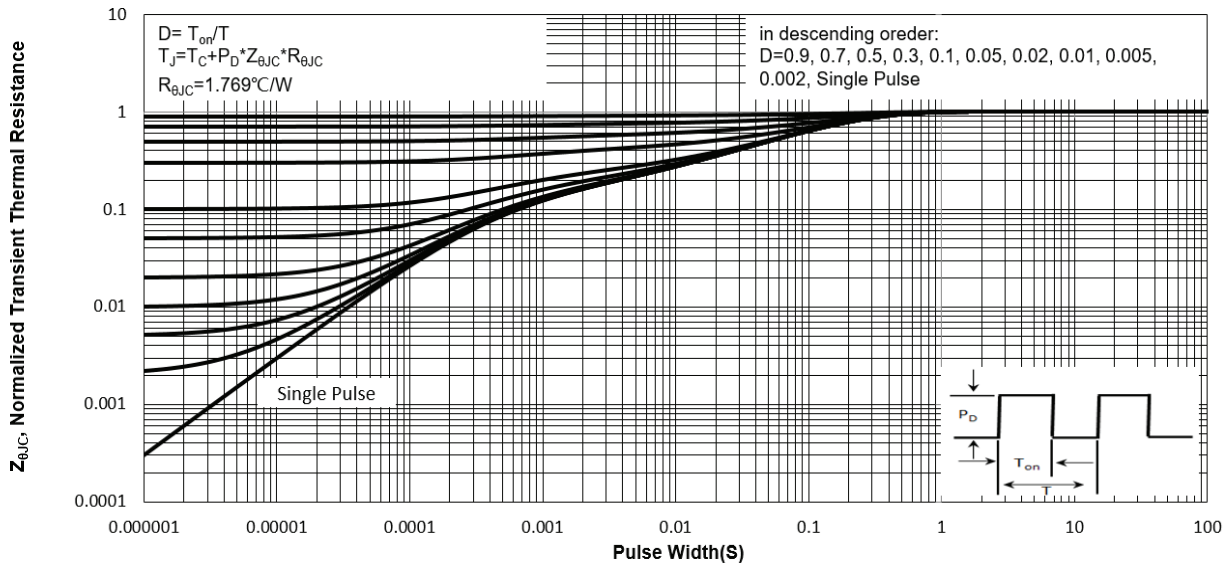
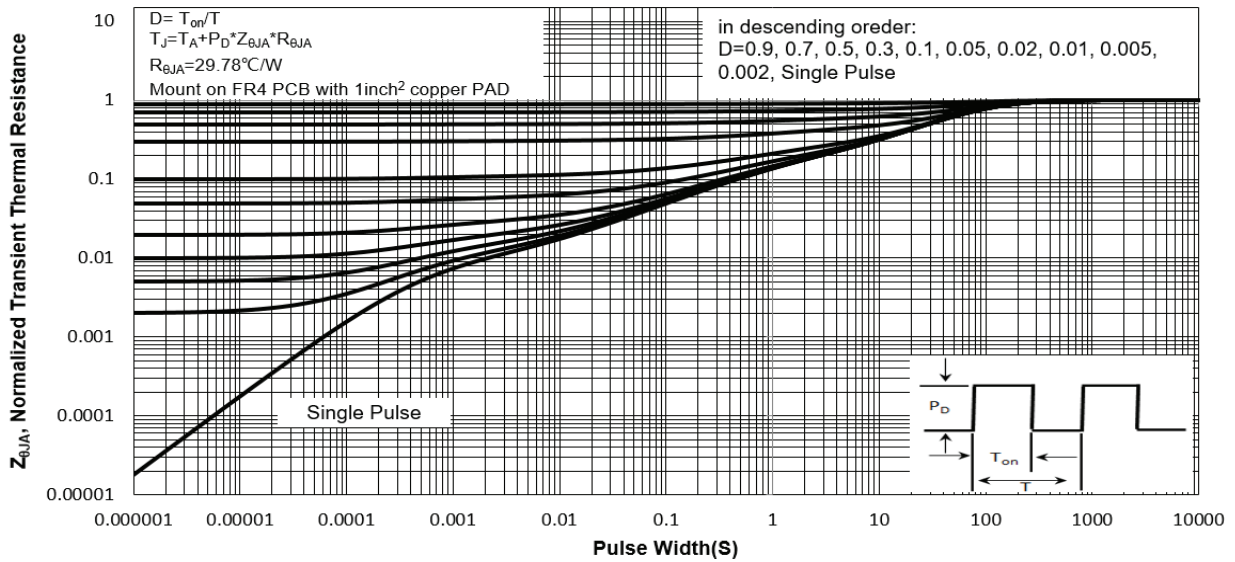


Fig. 14 Normalized Maximum Transient Thermal Impedance($Z_{\theta JA}$)



Test Circuits

Fig.1-1 Switching times test circuit

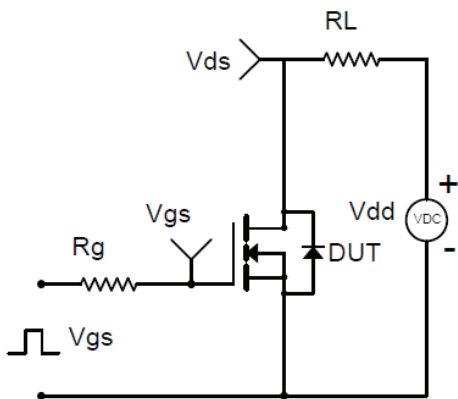


Fig.1-2 Switching Waveform

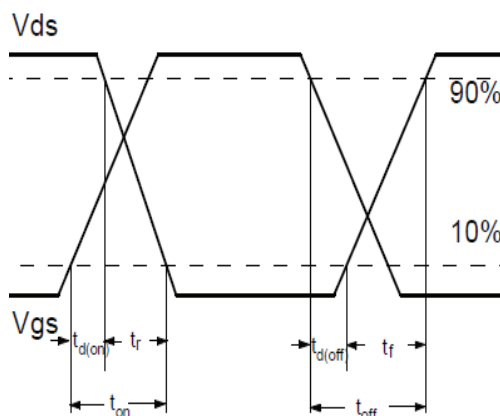


Fig.2-1 Gate charge test circuit

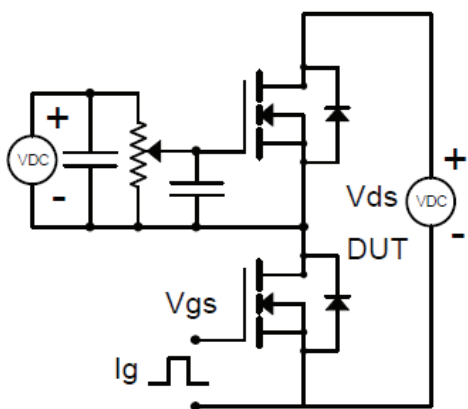


Fig.2-2 Gate charge waveform

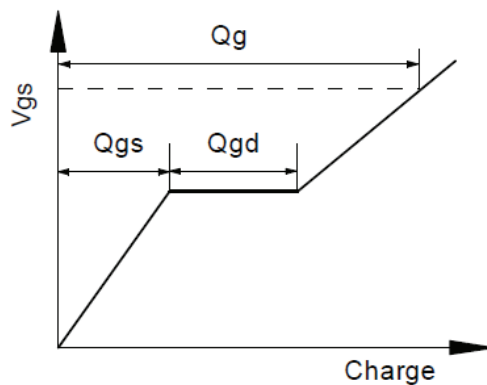


Fig.3-1 Avalanche test circuit

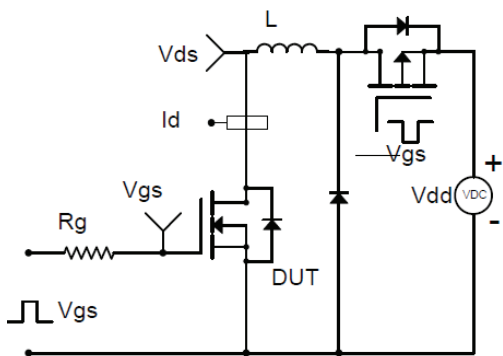
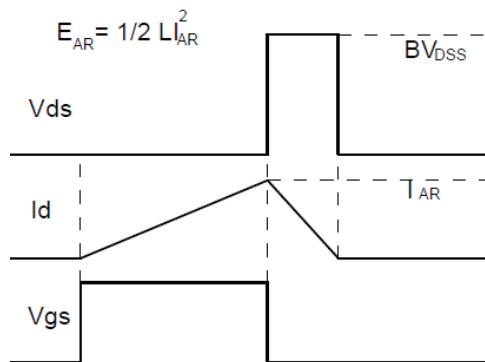
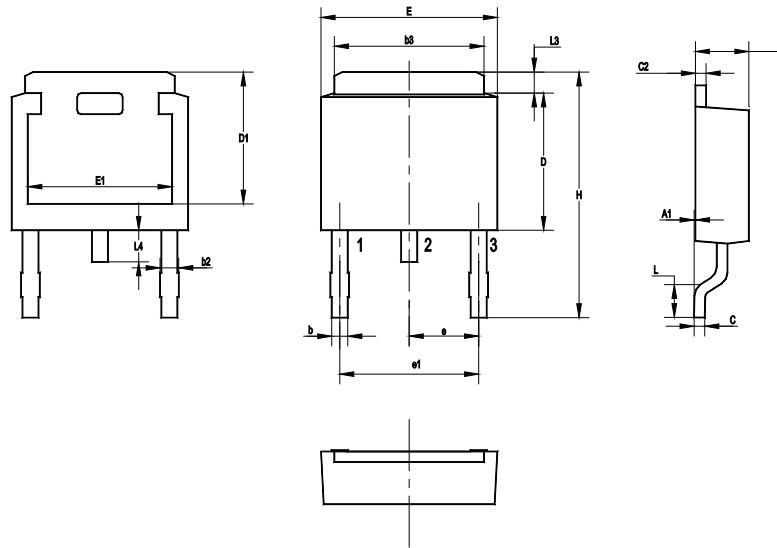


Fig.3-2 Avalanche waveform



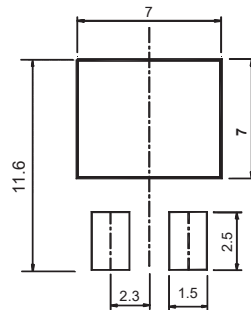
Package Outline Dimensions (Units: mm)

TO-252



UNIT	A	A1	b	b2	b3	C	C2	D	D1	E	E1	e	e1	H	L	L3	L4
mm	2.5	0.15	1.0	1.15	5.5	0.65	0.65	6.2	5.4	6.7	5.0	2.30	4.60	10.7	1.78	1.20	1.10
	2.1	0	0.5	0.65	4.9	0.4	0.4	5.6	5.0	6.1	4.6	TYP.	TYP.	9	1.40	0.85	0.51

Recommended Soldering Footprint



Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
TO-252	16	8 ± 0.1	0.315 ± 0.004	330	13	2,500

Marking information

" SFTN8046R " = Part No.
 " ***** " = Date Code Marking
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Electrical Characteristics Curves

Fig. 7 Typical Junction Capacitance

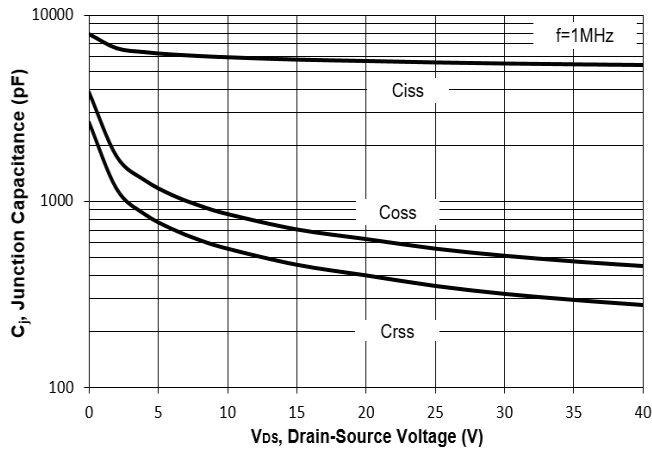


Fig. 8 Drain-Source Leakage Current vs. Tj

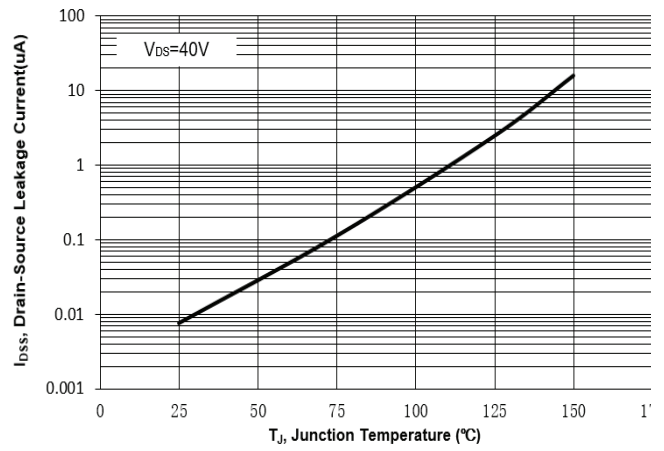


Fig. 9 V(BR)DSS vs. Junction Temperature

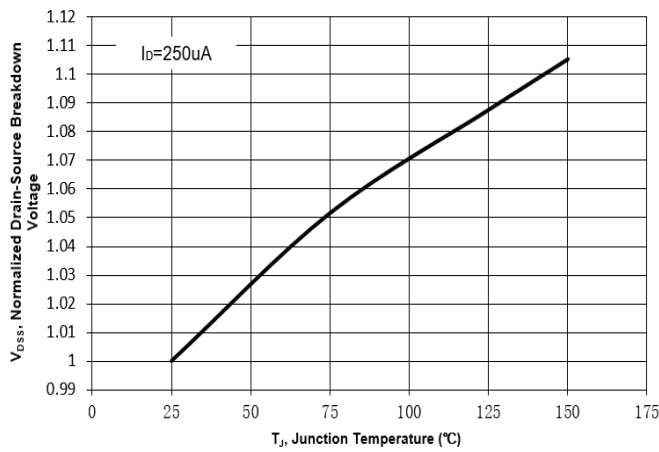


Fig. 10 Gate Threshold Variation vs. Tj

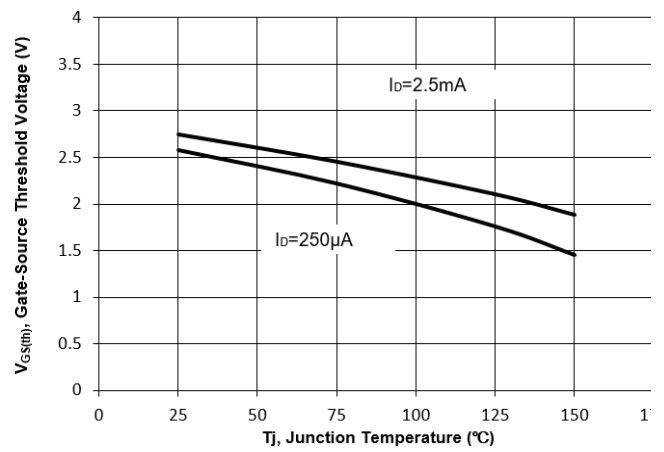


Fig. 11 Gate Charge

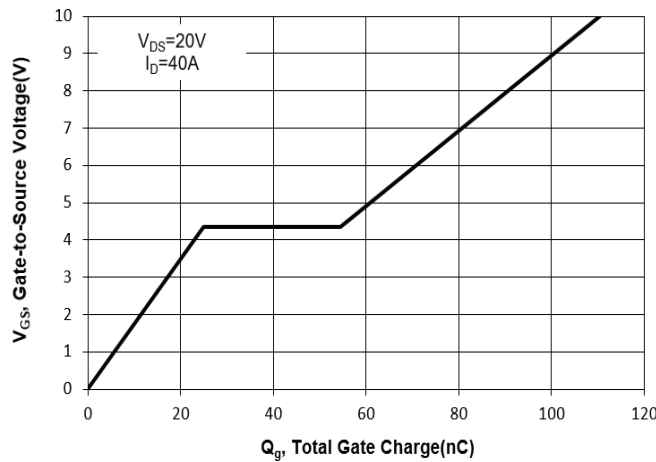


Fig. 12 Safe Operation Area

